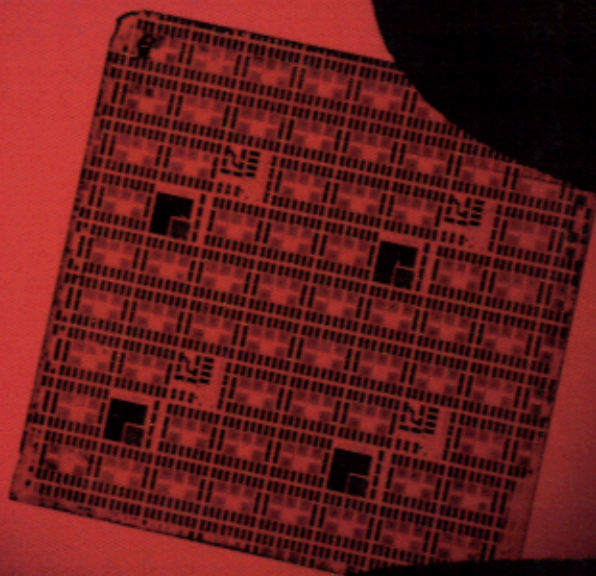


an introduction to
semiconductor devices



donald neamen

M c G R A W - H I L L I N T E R N A T I O N A L E D I T I O N



CONTENTS

Preface xvii

CHAPTER 1

The Crystal Structure of Solids 1

1.0 Preview 1

1.1 Semiconductor Materials 2

1.2 Types of Solids 3

1.3 Space Lattices 4

1.3.1 Primitive and Unit Cell 4

1.3.2 Basic Crystal Structures 6

1.3.3 Crystal Planes and Miller Indices 7

1.3.4 The Diamond Structure 13

1.4 Atomic Bonding 15

1.5 Imperfections and Impurities in Solids 17

1.5.1 Imperfections in Solids 17

1.5.2 Impurities in Solids 18

Σ 1.6 Growth of Semiconductor Materials 19

1.6.1 Growth from a Melt 20

1.6.2 Epitaxial Growth 22

Σ 1.7 Device Fabrication Techniques:

Oxidation 23

1.8 Summary 25

Problems 27

CHAPTER 2

Theory of Solids 31

2.0 Preview 31

2.1 Principles of Quantum Mechanics 32

2.1.1 Energy Quanta 32

2.1.2 Wave-Particle Duality Principle 34

2.2 Energy Quantization and Probability Concepts 36

2.2.1 Physical Meaning of the Wave Function 36

2.2.2 The One-Electron Atom 37

2.2.3 Periodic Table 40

2.3 Energy-Band Theory 41

2.3.1 Formation of Energy Bands 41

2.3.2 The Energy Band and the Bond Model 45

2.3.3 Charge Carriers—Electrons and Holes 47

2.3.4 Effective Mass 49

2.3.5 Metals, Insulators, and Semiconductors 50

2.3.6 The k -Space Diagram 52

2.4 Density of States Function 55

2.5 Statistical Mechanics 57

2.5.1 Statistical Laws 57

2.5.2 The Fermi-Dirac Distribution Function and the Fermi Energy 58

2.5.3 Maxwell-Boltzmann Approximation 62

2.6 Summary 64

Problems 65

CHAPTER 3

The Semiconductor in Equilibrium 70

3.0 Preview 70

3.1 Charge Carriers in Semiconductors 71

3.1.1 Equilibrium Distribution of Electrons and Holes 72

3.1.2 The n_0 and p_0 Equations 74

3.1.3 The Intrinsic Carrier Concentration 79

3.1.4 The Intrinsic Fermi-Level Position 82

3.2 Dopant Atoms and Energy Levels 83

3.2.1 Qualitative Description 83

3.2.2 Ionization Energy 86

3.2.3 Group III-V Semiconductors 88

3.3 Carrier Distributions in the Extrinsic Semiconductor 89

3.3.1 Equilibrium Distribution of Electrons and Holes 89

3.3.2	The $n_0 p_0$ Product	93
Σ 3.3.3	The Fermi–Dirac Integral	94
3.3.4	Degenerate and Nondegenerate Semiconductors	96
3.4	Statistics of Donors and Acceptors	97
3.4.1	Probability Function	98
Σ 3.4.2	Complete Ionization and Freeze-Out	99
3.5	Carrier Concentrations—Effects of Doping	102
3.5.1	Compensated Semiconductors	102
3.5.2	Equilibrium Electron and Hole Concentrations	102
3.6	Position of Fermi Energy Level—Effects of Doping and Temperature	109
3.6.1	Mathematical Derivation	109
3.6.2	Variation of E_F with Doping Concentration and Temperature	112
3.6.3	Relevance of the Fermi Energy	114
Σ 3.7	Device Fabrication Technology: Diffusion and Ion Implantation	115
3.7.1	Impurity Atom Diffusion	116
3.7.2	Impurity Atom Ion Implantation	118
3.8	Summary	119
	Problems	121
CHAPTER 4		
Carrier Transport and Excess Carrier Phenomena 128		
4.0	Preview	128
4.1	Carrier Drift	129
4.1.1	Drift Current Density	129
4.1.2	Mobility Effects	132
4.1.3	Semiconductor Conductivity and Resistivity	137
4.1.4	Velocity Saturation	143
4.2	Carrier Diffusion	145
4.2.1	Diffusion Current Density	145
4.2.2	Total Current Density	148
4.3	Graded Impurity Distribution	149
4.3.1	Induced Electric Field	149
4.3.2	The Einstein Relation	152
4.4	Carrier Generation and Recombination	153
4.4.1	The Semiconductor in Equilibrium	154
4.4.2	Excess Carrier Generation and Recombination	155
4.4.3	Generation–Recombination Processes	158
Σ 4.5	The Hall Effect	161
4.6	Summary	164
	Problems	166
CHAPTER 5		
The pn Junction and Metal–Semiconductor Contact 174		
5.0	Preview	174
5.1	Basic Structure of the pn Junction	175
5.2	The pn Junction—Zero Applied Bias	176
5.2.1	Built-In Potential Barrier	177
5.2.2	Electric Field	179
5.2.3	Space Charge Width	183
5.3	The pn Junction—Reverse Applied Bias	185
5.3.1	Space Charge Width and Electric Field	186
5.3.2	Junction Capacitance	189
5.3.3	One-Sided Junctions	192
5.4	Metal–Semiconductor Contact—Rectifying Junction	194
5.4.1	The Schottky Barrier	194
5.4.2	The Schottky Junction—Reverse Bias	196
5.5	Forward Applied Bias—An Introduction	197
5.5.1	The pn Junction	197
5.5.2	The Schottky Barrier Junction	199
5.5.3	Comparison of the Schottky Diode and the pn Junction Diode	201
Σ 5.6	Metal–Semiconductor Ohmic Contacts	203
Σ 5.7	Nonuniformly Doped pn Junctions	206
5.7.1	Linearly Graded Junctions	206
5.7.2	Hyperabrupt Junctions	208
Σ 5.8	Device Fabrication Techniques: Photolithography, Etching, and Bonding	210

5.8.1	<i>Photomasks and Photolithography</i>	210
5.8.2	<i>Etching</i>	211
5.8.3	<i>Impurity Diffusion or Ion Implantation</i>	211
5.8.4	<i>Metallization, Bonding, and Packaging</i>	211
5.9	Summary	212
	Problems	215

CHAPTER 6

Fundamentals of the Metal–Oxide–Semiconductor Field-Effect Transistor 223

6.0	Preview	223
6.1	The MOS Field-Effect Transistor Action	224
6.1.1	<i>Basic Principle of Operation</i>	225
6.1.2	<i>Modes of Operation</i>	226
6.1.3	<i>Amplification with MOSFETs</i>	226
6.2	The Two-Terminal MOS Capacitor	227
6.2.1	<i>Energy-Band Diagrams and Charge Distributions</i>	228
6.2.2	<i>Depletion Layer Thickness</i>	235
6.3	Potential Differences in the MOS Capacitor	239
6.3.1	<i>Work Function Differences</i>	240
6.3.2	<i>Oxide Charges</i>	244
6.3.3	<i>Flat-Band Voltage</i>	245
6.3.4	<i>Threshold Voltage</i>	247
Σ 6.3.5	<i>Electric Field Profile</i>	254
6.4	Capacitance–Voltage Characteristics	258
6.4.1	<i>Ideal C–V Characteristics</i>	258
Σ 6.4.2	<i>Frequency Effects</i>	263
Σ 6.4.3	<i>Fixed Oxide and Interface Charge Effects</i>	264
6.5	The Basic MOSFET Operation	268
6.5.1	<i>MOSFET Structures</i>	268
6.5.2	<i>Current–Voltage Relationship—Basic Concepts</i>	270
Σ 6.5.3	<i>Current–Voltage Relationship—Mathematical Derivation</i>	282
6.5.4	<i>Substrate Bias Effects</i>	287

6.6	Small-Signal Equivalent Circuit and Frequency Limitation Factors	290
6.6.1	<i>Transconductance</i>	290
6.6.2	<i>Small-Signal Equivalent Circuit</i>	291
6.6.3	<i>Frequency Limitation Factors and Cutoff Frequency</i>	293
Σ 6.7	Device Fabrication Techniques	296
6.7.1	<i>Fabrication of an NMOS Transistor</i>	296
6.7.2	<i>The CMOS Technology</i>	297
6.8	Summary	299
	Problems	301

CHAPTER 7

Metal–Oxide–Semiconductor Field-Effect Transistor: Additional Concepts 311

7.0	Preview	311
7.1	MOSFET Scaling	312
7.1.1	<i>Constant-Field Scaling</i>	312
7.1.2	<i>Threshold Voltage—First Approximation</i>	313
7.1.3	<i>Generalized Scaling</i>	314
7.2	Nonideal Effects	315
7.2.1	<i>Subthreshold Conduction</i>	315
7.2.2	<i>Channel Length Modulation</i>	318
7.2.3	<i>Mobility Variation</i>	321
7.2.4	<i>Velocity Saturation</i>	324
7.3	Threshold Voltage Modifications	326
7.3.1	<i>Short-Channel Effects</i>	327
7.3.2	<i>Narrow-Channel Effects</i>	331
7.3.3	<i>Substrate Bias Effects</i>	333
7.4	Additional Electrical Characteristics	335
7.4.1	<i>Oxide Breakdown</i>	335
7.4.2	<i>Near Punch-Through or Drain-Induced Barrier Lowering</i>	335
7.4.3	<i>Hot Electron Effects</i>	337
7.4.4	<i>Threshold Adjustment by Ion Implantation</i>	338
7.5	Device Fabrication Techniques: Specialized Devices	341
7.5.1	<i>Lightly Doped Drain Transistor</i>	342
7.5.2	<i>The MOSFET on Insulator</i>	343

- 7.5.3 *The Power MOSFET* 345
- 7.5.4 *MOS Memory Device* 348

7.6 Summary 350

Problems 352

CHAPTER 8

Nonequilibrium Excess Carriers in Semiconductors 358

- 8.0 Preview 358
- 8.1 Carrier Generation and Recombination 359
- 8.2 Analysis of Excess Carriers 360
 - 8.2.1 *Continuity Equations* 361
 - 8.2.2 *Time-Dependent Diffusion Equations* 362
- 8.3 Ambipolar Transport 364
 - 8.3.1 *Derivation of the Ambipolar Transport Equation* 364
 - 8.3.2 *Limits of Extrinsic Doping and Low Injection* 366
 - 8.3.3 *Applications of the Ambipolar Transport Equation* 368
 - 8.3.4 *Dielectric Relaxation Time Constant* 376
 - 8.3.5 *Haynes-Shockley Experiment* 379
- 8.4 Quasi-Fermi Energy Levels 382
- 8.5 Excess Carrier Lifetime 385
 - 8.5.1 *Shockley-Read-Hall Theory of Recombination* 385
 - 8.5.2 *Limits of Extrinsic Doping and Low Injection* 387
- 8.6 Surface Effects 389
 - 8.6.1 *Surface States* 389
 - 8.6.2 *Surface Recombination Velocity* 390
- 8.7 Summary 391
- Problems 392

CHAPTER 9

The pn Junction and Schottky Diodes 398

- 9.0 Preview 398
- 9.1 The pn and Schottky Barrier Junctions Revisited 399

- 9.1.1 *The pn Junction* 399
- 9.1.2 *The Schottky Barrier Junction* 402

9.2 The pn Junction—Ideal Current–Voltage Relationship 404

- 9.2.1 *Boundary Conditions* 404
- 9.2.2 *Minority-Carrier Distribution* 409
- 9.2.3 *Ideal pn Junction Current* 411
- 9.2.4 *Summary of Physics* 416
- 9.2.5 *Temperature Effects* 418
- 9.2.6 *The “Short” Diode* 420
- 9.2.7 *Summary of Results* 422

9.3 The Schottky Barrier Junction—Ideal Current–Voltage Relationship 423

- 9.3.1 *The Schottky Diode* 423
- 9.3.2 *Comparison of the Schottky Diode and the pn Junction Diode* 426

9.4 Small-Signal Model of the pn Junction 428

- 9.4.1 *Diffusion Resistance* 428
- 9.4.2 *Small-Signal Admittance* 430
- 9.4.3 *Equivalent Circuit* 432

9.5 Generation-Recombination Currents 434

- 9.5.1 *Reverse-Bias Generation Current* 434
- 9.5.2 *Forward-Bias Recombination Current* 437
- 9.5.3 *Total Forward-Bias Current* 439

9.6 Junction Breakdown 441

9.7 Charge Storage and Diode Transients 446

- 9.7.1 *The Turn-Off Transient* 446
- 9.7.2 *The Turn-On Transient* 449

9.8 Summary 449

Problems 451

CHAPTER 10

The Bipolar Transistor 460

10.0 Preview 460

10.1 The Bipolar Transistor Action 461

- 10.1.1 *The Basic Principle of Operation* 462
- 10.1.2 *Simplified Transistor Current Relations* 466
- 10.1.3 *The Modes of Operation* 468
- 10.1.4 *Amplification with Bipolar Transistors* 470

10.2	Minority-Carrier Distribution	472	11.2	Heterojunctions	560
10.2.1	Forward-Active Mode	472	11.2.1	The Heterojunction	560
10.2.2	Other Modes of Operation	480	11.2.2	Heterojunction Bipolar Transistors	564
10.3	Low-frequency Common-Base Current Gain	483	11.2.3	High-Electron Mobility Transistor	566
10.3.1	Contributing Factors	483	11.3	The Thyristor	567
10.3.2	Mathematical Derivation of Current Gain Factors	486	11.3.1	The Basic Characteristics	568
10.3.3	Summary and Review	489	11.3.2	Triggering the SCR	570
10.3.4	Example Calculations of the Gain Factors	490	11.3.3	Device Structures	574
10.4	Nonideal Effects	495	11.4	Additional MOSFET Concepts	578
10.4.1	Base Width Modulation	495	11.4.1	Latch-Up	578
10.4.2	High Injection	499	11.4.2	Breakdown	580
10.4.3	Emitter Bandgap Narrowing	501	11.5	Microelectromechanical Systems (MEMS)	583
10.4.4	Current Crowding	503	11.5.1	Accelerometers	583
Σ 10.4.5	Nonuniform Base Doping	506	11.5.2	Inkjet Printing	584
10.4.6	Breakdown Voltage	507	11.5.3	Biomedical Sensors	584
10.5	Hybrid- π Equivalent Circuit Model	513	11.6	Summary	586
10.6	Frequency Limitations	517	Problems	587	
10.6.1	Time-Delay Factors	517			
10.6.2	Transistor Cutoff Frequency	519			
Σ 10.7	Large-Signal Switching	522			
Σ 10.8	Device Fabrication Techniques	524			
10.8.1	Polysilicon Emitter BJT	524			
10.8.2	Fabrication of Double-Polysilicon npn Transistor	525			
10.8.3	Silicon-Germanium Base Transistor	527			
10.8.4	The Power BJT	529			
10.9	Summary	533			
Problems	535				
 CHAPTER 11					
Additional Semiconductor Devices and Device Concepts 546					
11.0	Preview	546			
11.1	The Junction Field-Effect Transistor	547			
11.1.1	The pn JFET	547			
11.1.2	The MESFET	551			
11.1.3	Electrical Characteristics	553			
			CHAPTER 12		
			Optical Devices 590		
			12.0	Preview	590
			12.1	Optical Absorption	591
			12.1.1	Photon Absorption Coefficient	591
			12.1.2	Electron-Hole Pair Generation Rate	594
			12.2	Solar Cells	596
			12.2.1	The pn Junction Solar Cell	596
			12.2.2	Conversion Efficiency and Solar Concentration	599
			12.2.3	The Heterojunction Solar Cell	601
			12.2.4	Amorphous Silicon Solar Cells	603
			12.3	Photodetectors	605
			12.3.1	Photoconductor	605
			12.3.2	Photodiode	608
			12.3.3	PIN Photodiode	611
			12.3.4	Avalanche Photodiode	614
			12.3.5	Phototransistor	614
			12.4	Light-Emitting Diodes	616
			12.4.1	Generation of Light	616

12.4.2	<i>Internal Quantum Efficiency</i>	616
12.4.3	<i>External Quantum Efficiency</i>	618
12.4.4	<i>LED Devices</i>	620
12.5	Laser Diodes	622
12.5.1	<i>Stimulated Emission and Population Inversion</i>	622
12.5.2	<i>Optical Cavity</i>	625
12.5.3	<i>Threshold Current</i>	627
12.5.4	<i>Device Structures and Characteristics</i>	627
12.6	Summary	629
	Problems	631

APPENDIX A	
Selected List of Symbols	636

APPENDIX B	
System of Units, Conversion Factors, and General Constants	643

APPENDIX C	
The Periodic Table	647

APPENDIX D	
Unit of Energy—The Electron-Volt	648

APPENDIX E	
“Derivation” and Applications of Schrödinger’s Wave Equation	650

APPENDIX F	
Answers to Selected Problems	656
Index	663